


<b>INFORMATION DISCLOSURE CITATION IN AN APPLICATION</b>  (PTO-1449)				ATTY. DOCKET NO. 004393 USA C/01/MTCG/PCTRL		SERIAL NO. 10/686,589	
				APPLICANT Sasson R. SOMEKH et al.			
				FILING DATE October 17, 2003		GROUP 2125	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE	
<i>11/1</i>	6,381,564 B1	04/30/02	David et al.			05/03/99	
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<i>11/1</i>	6,735,492 B2	05/11/04	Conrad et al.			07/19/02	
EXAMINER <i>[Signature]</i>			DATE CONSIDERED <i>5/1/05</i>				

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<p align="center"><b>OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)</b></p>		
<p><i>MM</i></p>	<p>September 15, 2004. Office Action for U.S. Serial No. 10/632,107, filed August 1, 2003.</p>	
<p><i>J</i></p>	<p>September 29, 2004. Office Action for U.S. Serial No. 09/363,966, filed July 29, 1999.</p>	
<p><i>J</i></p>	<p>October 1, 2004. International Preliminary Examination Report for PCT Serial No. PCT/US03/23964.</p>	
<p><i>J</i></p>	<p>October 6, 2004. Office Action for U.S. Serial No. 10/759,108, filed January 20, 2004.</p>	
<p><i>J</i></p>	<p>October 12, 2004. International Preliminary Examination Report for PCT Serial No. PCT/US02/19061.</p>	
<p><i>MM</i></p>	<p>November 17, 2004. Written Opinion for PCT Serial No. PCT/US01/27407.</p>	
<p>EXAMINER <i>[Signature]</i></p>	<p>DATE CONSIDERED <i>5/1/05</i></p>	

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Sasson R. SOMEKH et al.

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**U.S. PATENT DOCUMENTS**

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<b>FOREIGN PATENT DOCUMENTS</b>							
EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						Yes	No
<i>Mu</i>	EP 0 932 195 A1	07/28/99	EP			X	
	EP 1 083 470 A2	03/14/01	EP			X	
	GB 2 365 215 A	02/13/02	GB			X	
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